

General Description

The H is P-Channel enhancement mode power MOSFET which is produced with high cell density and DMOS trench technology .This device particularly suits low voltage applications, especially for battery powered circuits, the tiny and thin outline saves PCB consumption. are electrically identical.

-RoHS Compliant

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

Product Summery

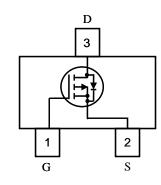
BVDSS	RDSON	ID
-20V	155mΩ	-1.6A

Applications

- High Frequency Point-of-Load Synchronous s Small power switching for MB/NB/UMPC/VGA
- A Switch and Battery Switch for Portable Devices
- Load Switch

SOT-323 Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	±12	V
I _D @T _c =25℃	Continuous Drain Current, V _{GS} @ -4.5V ¹	-1.6	А
I _{DM}	Pulsed Drain Current ²	-5	А
P _D @T _A =25°C	Total Power Dissipation ³	350	mW
T _{STG}	Storage Temperature Range	-55 to 150	$^{\circ}\!\mathbb{C}$
TJ	Operating Junction Temperature Range	-55 to 150	°C



Electrical Characteristics (T_J=25 C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V_{GS} =0V , I_D =-250uA	-20			V	
	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V , I _D =-1A		145	155	mΩ	
R _{DS(ON)}		V _{GS} =-2.5V , I _D =-0.5A		150	168		
		V _{GS} =-1.8V , I _D =-0.3A		180	220		
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, I_D =-250uA	-0.4	-0.7	-1	V	
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-20V , V _{GS} =0V , T _J =25℃			-1	uA	
I _{GSS}	Gate-Source Leakage Current V _{GS} =±12V , V _{DS} =0V				±100	nA	
gfs	Forward Transconductance V _{DS} =-5V , I _D =-2A			5		S	
Qg	Total Gate Charge (-4.5V)			4.9			
Q _{gs}	Gate-Source Charge V _{DS} =-6V , V _{GS} =-4.5V , I _D =-2.8A			0.62		nC	
Q_{gd}	Gate-Drain Charge			1.07			
$T_{d(on)}$	Turn-On Delay Time			10.1			
Tr	Rise Time	V _{DS} =-6V , V _{GS} =-4.5V ,		4.76		ns	
$T_{d(off)}$	Turn-Off Delay Time	R_{GEN} =6 Ω , RL =6 Ω ,		84.1			
T _f	Fall Time			25.2			
C _{iss}	Input Capacitance			472			
C _{oss}	Output Capacitance	V _{DS} =-6V , V _{GS} =0V , f=1MHz		71		pF	
C _{rss}	Reverse Transfer Capacitance			51			

Note:

^{1.} The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, t<10 sec.

^{2.}The data tested by pulsed , pulse width $\,\leq\,300\text{us}$, duty cycle $\,\leq\,2\%$

 $[\]textbf{4.The data is theoretically the same as } \textbf{I}_{D} \text{ and } \textbf{I}_{DM} \text{ , in real applications , should be limited by total power dissipation.}$



Typical Characteristics

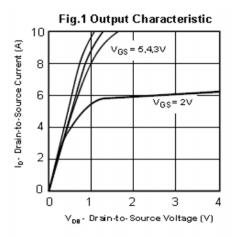


Fig.3 On-Resistance Variation with Temperature

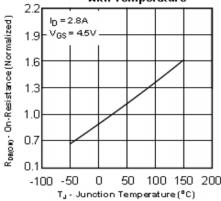


Fig.5 Gate Threshold Variation with Temperature

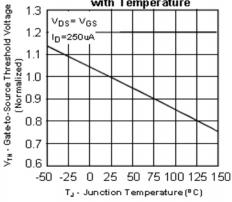


Fig.2 Transfer Characteristics

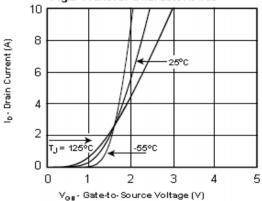
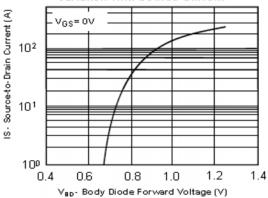
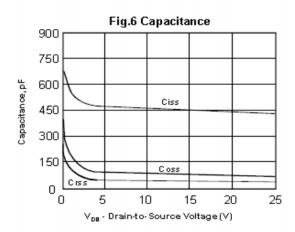
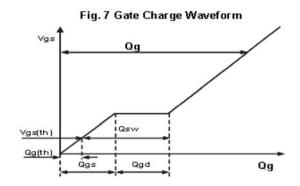


Fig.4 Body Diode Forward Voltage Variation with Source Current









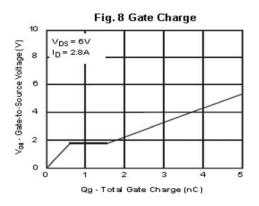
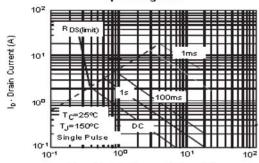
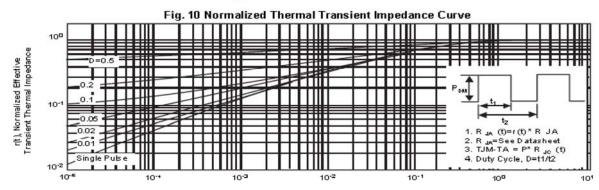


Fig. 9 Maximum Safe Operating Area



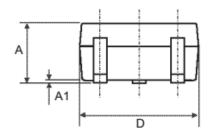
 V_{DB} - Drain-to-Source Voltage (V)

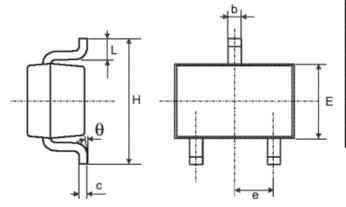


Square Wave Pulse Duration (sec)



SOT-323 Package Outline Dimensions





	DIMENSIONS					
REF.	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	0.8		1.1	0.031		0.043
A1	0.0		0.1	0.0		0.004
b	0.25		0.4	0.010		0.016
С	0.1		0.26	0.004		0.010
D	1.8	2.0	2.2	0.071	0.079	0.086
Е	1.15	1.25	1.35	0.045	0.049	0.053
е		0.65			0.026	
Н	1.8	2.1	2.4	0.071	0.083	0.094
L	0.1	0.2	0.3	0.004	0.008	0.012
θ	0		30°	0		30°



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